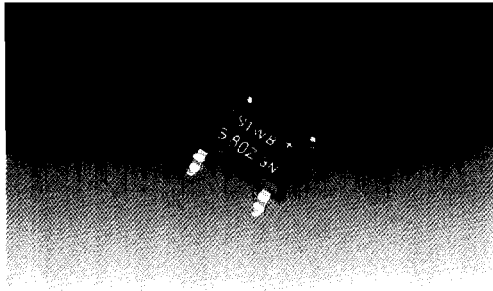
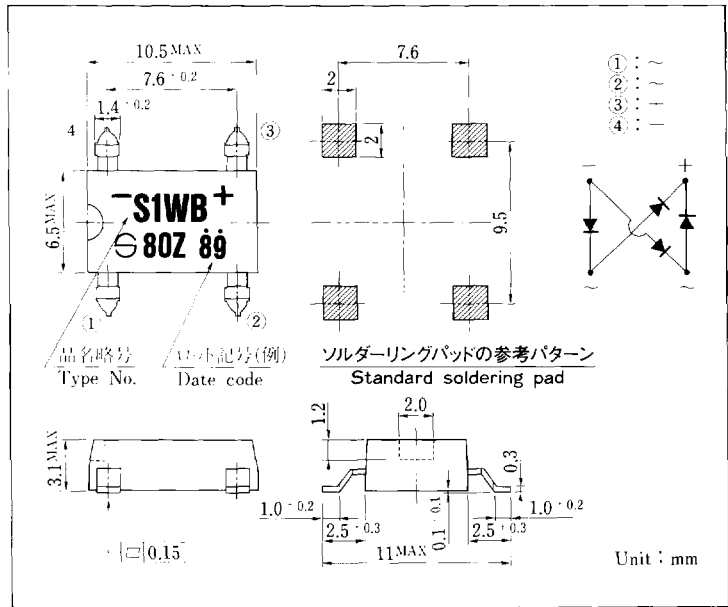


S1WB(A)□Z

800V 1A



■ 外形寸法図 OUTLINE DIMENSIONS



■ 定格表 RATINGS

絶対最大定格 Absolute Maximum Ratings

項目 Item	記号 Symbol	条件 Conditions	品名 Type No.		単位 Unit
			S1WB(A)□Z		
			80		
保存温度 Storage Temperature	Tstg		-40~150		°C
接合部温度 Operating Junction Temperature	Tj		150		°C
せん頭逆電圧 Maximum Reverse Voltage	VRM		800		V
出力電流 Average Rectified Forward Current	IO	50Hz正弦波, 抵抗負荷, Ta=25°C 50Hz sine wave, R-load, Ta=25°C	1		A
せん頭サージ順電流 Peak Surge Forward Current	IFSM	50Hz正弦波, 非繰り返し1サイクルせん頭値, Tj=25°C 50Hz sine wave, Non-repetitive 1 cycle peak value, Tj=25°C	30		A
電流2乗時間積 Current Squared Time	I ² t	1ms ≤ t < 10ms Tc=25°C	2.5		A ² s
せん頭サージ逆電力 Peak Surge Reverse Power	PRSM	パルス幅10μs, 非繰り返し, 1素子当り, Tj=25°C Pulse width 10μs, Non-repetitive, Rating of per diode, Tj=25°C	1		kW

電氣的・熱的特性 Electrical Characteristics (Tl=25°C)

順電圧 Forward Voltage	VF	IF=0.5A, パルス測定, 1素子当りの規格値 Pulse measurement, Rating of per diode	MAX	1.0	V
逆電流 Reverse Current	IR	VR=VRM, パルス測定, 1素子当りの規格値 Pulse measurement, Rating of per diode	MAX	10	μA
降伏電圧 Avalanche Voltage	VZ	IR=0.6mA, 1素子当りの規格値 Rating of per diode	MIN	1000	V
熱抵抗 Thermal Resistance	θjl	接合部・リード間 Between junction and lead	MAX	10	°C/W
	θja	接合部・周囲間 Between junction and ambient	MAX	65	

■ 特性図 CHARACTERISTIC DIAGRAMS

